
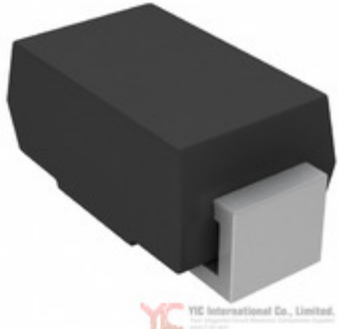


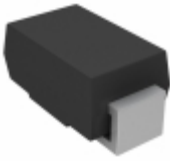

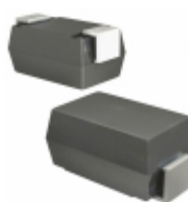
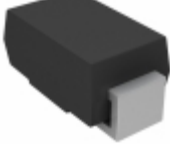
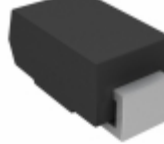
| | |
|---|--|
|  | <h2>US1B-E3/61T</h2> |
| | <p>Hersteller-Teilenummer: US1B-E3/61T</p> <p>Hersteller / Marke: Vishay / Semiconductor - Diodes Division</p> <p>Teil der Beschreibung: DIODE GEN PURP 100V 1A DO214AC</p> <p>Datenblätter: 1.US1B-E3/61T.pdf 2.US1B-E3/61T.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 157970 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
|  | |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

| | |
|------------------------------------|---|
| Teilenummer | US1B-E3/61T |
| Hersteller | Vishay / Semiconductor - Diodes Division |
| Beschreibung | DIODE GEN PURP 100V 1A DO214AC |
| Kategorie | Diskrete Halbleiterprodukte > Dioden-Gleichrichter- |
| Teilstatus | 157970 pcs Stock |
| Serie | - |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | DO-214AC, SMA |
| Supplier Device-Gehäuse | DO-214AC (SMA) |
| Diodentyp | Standard |
| Strom - Richt (Io) | 1A |
| Spannung - Forward (Vf) (Max) @ If | 1V @ 1A |
| Strom - Sperrleckstrom @ Vr | 10µA @ 100V |
| Spannung - Sperr (Vr) (max) | 100V |
| Geschwindigkeit | Fast Recovery = 200mA (Io) |
| Rückwärts-Erholzeit (Trr) | 50ns |
| Betriebstemperatur - Anschluss | -55°C ~ 150°C |
| Kapazität @ Vr, F | 15pF @ 4V, 1MHz |
| Verpackung | Tape & Reel (TR) |

US1B-E3/61T ist neu im Original, Suche US1B-E3/61T Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie US1B-E3/61T Vishay / Semiconductor - Diodes Division mit Garantie und Vertrauen. Anfrage US1B-E3/61T: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|--|---|--|--|
|  <p>US1B-M3/61T Vishay / Semiconductor - Diodes Division DIODE 1A 100V 50NS DO-214AC</p> |  <p>US1B-E3 VISHAYMAS US1B-E3 VISHAYMAS</p> |  <p>US1B-13-F Diodes Incorporated DIODE GEN PURP 100V 1A SMA</p> |  <p>US1B-TP Micro Commercial Components (MCC) DIODE GEN PURP 100V 1A DO214AC</p> |
|  <p>US1B-M3/5AT Vishay / Semiconductor - Diodes Division DIODE 1A 100V 50NS DO-214AC</p> |  <p>US1B-E3/5AT Vishay / Semiconductor - Diodes Division DIODE GEN PURP 100V 1A DO214AC</p> |  <p>US1B-E3/5AT Electro-Films (EFI) / Vishay DIODE GEN PURP 100V 1A DO214AC</p> |  <p>US1B-E3/61T Electro-Films (EFI) / Vishay DIODE GEN PURP 100V 1A DO214AC</p> |

heiße Teile

Mehr

| | | | | |
|---------------|------------------------|---------------|---------------|---------------|
| ⚙ US168ELD | ➔ US168ESE | ➔ US1881ESO | D US1881KSE | ➔ US1881KSO |
| ⊣ US1881KUA | ⚙ US1881KUA-AAA-000-BU | D US1881LSO | ➔ US1A-13-F | ➔ US1A-E3/5AT |
| ⚙ US1A-E3/5AT | ⊣ US1A-E3/61T | ⚙ US1A-E3/61T | ➔ US1A-M3/61T | ➔ US1A-M3/61T |
| D US1AHE3/5AT | ⚙ US1AHE3/5AT | ⊣ US1AHE3/61T | ⚙ US1AHE3/61T | ➔ US1B-13-F |
| ➔ US1B-E3/5AT | ➔ US1B-E3/5AT | ⚙ US1B-E3/61T | ⊣ US1B-M3/61T | ➔ US1B-M3/61T |
| ➔ US1BHE3/5AT | ➔ US1BHE3/5AT | D US1BHE3/61T | ⚙ US1BHE3/61T | ⊣ US1C-E3/61T |
| ⚙ US1D-13-F | D US1D-E3/61T | ➔ US1D-E3/61T | ➔ US1D-M3/61T | ➔ US1D-M3/61T |
| ⊣ US1DWF-7 | ⚙ US1DWF-7 | ➔ US1G-13-F | ➔ US1G-E3/61T | ➔ US1G-E3/61T |
| ⚙ US1G-M3/61T | ⊣ US1G-M3/61T | ⚙ US1G/11T | D US1GHE3/5AT | ➔ US1GHE3/5AT |
| ➔ US1GHE3/61 | ⚙ US1GHE3/61T | ⊣ US1GHE3/61T | ⚙ US1GHE3_A/H | ➔ US1GHE3_A/H |

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited